

**LIST OF PATENTS AND OTHER ITEMS FOR APPLICANT'S
INFORMATION DISCLOSURE STATEMENT**

(Use several sheets if necessary)

ATTY. DOCKET NO.

659944-100001

SERIAL NO.

10767,402

APPLICANT:

Jou, Ming-Jiunn et al.

FILING DATE:

January 29, 2004

GROUP:

2879 2815

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF. NO.	DOCUMENT NUMBER	ISSUE DATE	NAME	CLASS	SUB CLASS	FILING DATE
<i>EP</i>	A	3,889,286	06/10/75	Debesis	357/67		12/26/73
	B	4,570,172	02/11/86	Henry et al.	357/17		12/19/83
	C	4,680,602	07/14/87	Watanabe et al.	357/17		09/06/84
	D	4,775,876	10/04/88	Moyer	357/17		09/08/87
	E	4,864,369	09/05/89	Snyder et al.	357/17		09/05/89
	F	4,918,497	04/17/90	Edmond	357/17		12/14/88
	G	5,048,035	09/10/91	Sugawara et al.	372/45		05/29/90
	H	5,138,404	08/11/92	Ishikawa et al.	357/16		05/31/91
	I	5,164,798	11/17/92	Huang	257/97		07/05/91
	J	5,233,204	08/03/93	Fletcher et al.	257/13		01/10/92
	K	5,300,791	04/05/94	Chen et al.	257/94		09/29/92
	L	5,359,209	10/25/94	Huang	257/94		12/09/93
	M	5,376,580	12/27/94	Kish et al.	437/127		03/19/93
	N	5,481,122	01/02/96	Jou et al.	257/9		07/25/94
	O	5,661,742	08/26/97	Huang et al.	372/46		05/22/96
	P	Re 35,665	11/18/97	Lin et al.	257/94		07/25/96
	Q	5,717,226	02/10/98	Lee et al.	257/86		09/18/96
	R	5,789,768	08/04/98	Lee et al.	257/96		06/23/97
	S	5,869,849	02/09/99	Jou et al.	257/96		10/05/95
	T	5,917,201	06/29/99	Ming-Jiunn et al.	257/94		09/04/97
<i>EP</i>	U	6,057,562	05/02/00	Lee et al.	257/96		04/18/97

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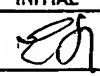

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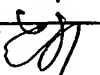
6-20-05


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	APPLICANT: Jou, Ming-Jiunn et al.	
	FILING DATE: January 29, 2004	GROUP: 2879-2815

	V	6,066,862	05/23/00	Chang et al.	257/103		08/31/98
	W	6,169,294 B1	01/02/01	Biing-Jye et al.	257/79		09/08/98
	X	6,225,648 B1	05/01/01	Hsieh et al.	257/95		07/09/99
	Y	6,552,367 B1	04/22/03	Hsieh et al.	257/94		10/06/00
	Z						

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL	REF. NO.	DOCUMENT NUMBER	PUBLICATION/ ISSUE DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANSLATION YES NO	
	AA	EPO 0 328 134 A2	02/10/89	EPO				
	AB	EPO 0 328 393 A2	02/09/89	EPO				
	AC	EPO 0 333 418 A2	03/14/89	EPO				
	AD	EPO 0 334 637 A2	03/22/89	EPO				
	AE	EPO 0 434 233 A1	11/23/90	EPO				
	AF	EPO 0 434 233 B1	11/23/90	EPO				
	AG	DE 198 17 368 A1	12/24/98	Germany				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
	AH	Woodall, J.M. et al., "Liquid Phase Epitaxial Growth of $Ga_{1-x}Al_xAs$," <i>J. Electrochem Soc.</i> , <u>116</u> (6), 899-903
	AI	Nuese, C.J. et al., "Optimization of Electroluminescent Efficiencies for Vapor-Grown $GaAs_{1-x}P_x$ Diodes," <i>J. Electrochem Soc.</i> , <u>116</u> (2), 248-253, 1969
	AJ	Chawla, B. et al., "Transition Region Capacitance of Diffused p-n Junctions," <i>IEEE Transactions On Electron Devices</i> , <u>18</u> (3) (1971)
	AK	Dierschke, L.E. et al., "Efficient Electroluminescence from Zinc-Diffused $Ga_{1-x}Al_xAs$ Diodes at 25°C," <i>Applied Phys.</i> <u>19</u> (4), 98-100 (1971)
	AL	Nuese, C.J. et al., "Orange Laser Emission and Bright Electroluminescence from $In_{1-x}Ga_xP$ Vapor-Grown p-n Junctions," <i>Appl. Phys. Lett.</i> , <u>20</u> (11), 431-433 (1972)
	AM	Berenbaum, L., "Effect of Oxygen on the Electromigration Behaviour of Al Thin Films," <i>Appl. Phys. Lett.</i> , <u>20</u> (11), 434 (1972)

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AN	Nuese, C.J., "The Preparation and Properties of Vapor-Grown $\text{In}_{1-x}\text{Ga}_x\text{P}$, <i>Metallurgical Transactions</i> , 2, 789-794 (1971)
AO	Hart, P.B., "Green and Yellow Emitting Devices in Vapor-Grown Gallium Phosphide," <i>Proceedings of the IEEE</i> , 61(7), 880-883 (1973)
AP	Kaneko, K. et al., "A New Method of Growing GaP Crystals for Light-Emitting Diodes," <i>Proceedings of the IEEE</i> , 61(7), 884 (1973)
AQ	Bergh et al., "Light Emitting Diodes, 1976 (Oxford University Press, Oxford)
AR	Nuese, C.J., "III-V Alloys For Optoelectronic Applications," <i>Journal of Electronic Materials</i> , 6(3), 253-293 (1976)
AS	Dawson, L.R., "High-efficiency graded-gand-gap $\text{Ga}_{1-x}\text{Al}_x\text{As}$ light-emitting," <i>J. Appl. Phys.</i> , 46(6), 2486-2492 (1977)
AT	Nishizawa, J. et al., "Minority-carrier lifetime measurements of efficient GaAlAs p-n heterojunctions," <i>J. Appl. Phys.</i> , 46(8), 3484-3495 (1977)
AU	Ishiguro, H. et al., "High efficient GaAls light-emitting diodes of 660 nm with a double heterostructure on a GaAlAs substrate," <i>Appl. Phys. Lett.</i> 43(11), 1034-1036 (1983)
AV	Kurata K. et al., "An Exprimental Study on Improvement of Performance for Hemispherically Shaped High-Power IRED's with $\text{Ga}_{1-x}\text{Al}_x\text{As}$ Grown Injunctions," <i>IEE Trans El. Dev</i> , ED-28(4) 374-379 (1981)
AW	Pilkuhn, M.H., "Light Emitting Diodes," 1981, Handbook on Semiconductors, Vol. 4 eds. T.S. Moss and C. Hilsum (North Holland Publishing Company, New York)
AX	Chopra, K.L. et al., "Transparent Conductors - A Status Review," <i>Thin Solid Films</i> 102, 1-46 (1983)
AY	Hing, I. et al., "High aluminum Composition AlGaInP Grown by Metalorganic Chemical Vapor Deposition - Impurity Doping and 590 nm (Orange) Electroluminescence, <i>Japanese Journal of Applied Physics</i> 23(9) 746-748 (1984)
AZ	Yuan J.S. et al., "Organometallic vapor phase epitaxial growth of AlGaInP," <i>J. Appl. Phys.</i> 57(4), 1380-1383 (1985)
BA	Watanabe, M. et al., "Interface properties for GaAs/InGaAlP heterojunctions by the capacitance-voltage profiling technique," <i>Appl. Phys. Lett</i> 50(14), 906-908 (1987)
BB	Tanaka et al., "Room Temperature Operation Of MBE-Grown InGaP/InGaAlP MOW Visible Laser Diodes," <i>Electronic Letters</i> , 22 (4)
BC	Bontemps, A. et al., "Laser annealing of Bi-implanted ZnTe," <i>Appl. Phys. Lett.</i> 36(7), 542-544 (1960)
BD	Kuo, C.P. et al., "High performance AlGaInP visible light-emitting diodes," <i>Appl. Phys. Lett</i> , 57(27), 2937-2939 (1990)
BE	Gillessen, K. et al., "Light Emitting Diodes," Prentice/Hall International
BF	Kuo, C.P. et al., "Stimulated Emission in $\text{In}_{0.5}(\text{Al}_x\text{Ga}_{1-x})_{0.5}\text{P}$ Quantum Well Heterostructures," <i>Journal of Crystal Growth</i> 93, 389-395 (1988)
BG	Konagai, M. et al., "Metallilc p-TYPE GaAs And GaAlAs Grown By Metalorganic Molecular Beam Epitaxy," <i>Journal of Crystal Growth</i> 98, 167-173 (1989)
BH	Duen Ho, F., "Space-charge layer capacitance and offset voltage of an exponential-constant p-n junction," <i>Int. J. Electronics</i> , 70(2), 327-342 (1991)
BI	Fletcher, R.M. et al., "The Growth and Properties of High Performance AlGaInP Emitters using a Lattice Mismatched GaP Window Layer," <i>Journal of Electronic Materials</i> , 26(12), 1125-1130 (1991)

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	BJ	Domen K., et al., "Study on radiative efficiency in AlGaInP/GaInP double-heterostructures: influence of deep level in cladding layers," <i>Journal of Crystal Growth</i> , 115 529-532 (1991)
	BK	Chen, T.P. et al., "AlGaInP green light emitting diode," <i>SPIE</i> 1813 136-141 (1992)
	BL	Huang et al, "Twofold efficiency improvement in high performance AlGaInP light-emitting diodes in the 555-620 nm spectral region using a thick GaP window layer," <i>Appl. Phys. Lett.</i> 61 (9), 1045-1047 (1992)
	BM	Gunshot, R.L. et al., "The molecular beam epitaxial growth of wide gap II-VI injection lasers and light-emitting diodes," <i>Thin Solid Films</i> 231 , 190-196 (1993)
	BN	Lin, J.F. et al., "Growth of GaP window layer on AlGaInP light-emitting diodes using misoriented substrates," <i>Crystal Growth</i>
	BO	Chi, G.C. et al., "Window layer for current spreading in AlGaInP light-emitting diode," <i>J. Appl. Phys.</i> 76 (5), 2600-2611 (1994)
	BP	Chang, S.J., "AlGaInP Yellow-Green Light-Emitting Diodes with a Tensile Strain Barrier Cladding Layer"
	BQ	Coldren, L.A. et al., "Diode Lasers and Photonic Integrated Circuits," John Wiley & Sons, Inc. (1995)-
	BR	Chang, S.J., et al., "AlGaInP/GaP Light-Emitting Diodes Fabricated by Wafer Direct Bonding Technology," <i>Jpn. J. Appl. Phys</i> 35 (5), 4199-4202 (1996)
	BS	Ta+gare, M.V. et al., "Heavy Be doping of GaP and In _x Ga _{1-x} P," <i>J. Vac. Sci Technol. B.</i> 14 (2), 2325-2326 (1996)
	BT	Tagare, M.V. et al., "Nonalloyed ohmic contacts to heavily Be-doped GaP and In _x Ga _{1-x} P," <i>Appl Phys. Lett.</i> 68 (24), 2485-2487 (1996)
	BU	Yang, J.W., "InGaN-GaN based light-emitting diodes over (111) spinel substrates," <i>Appl. Phys. Lett.</i> 69 (3), 369-370 (1996)
	BV	Chang, S.J. et al., "AlGaInP multiquantum well light-emitting diodes," <i>IEEE</i> 144 (6), 405-409 (1997)
	BW	Chang, S.J. et al., "AlGaInP-GaInP Compressively Strained Mutiquantum-Well Light-Emitting Diodes For Polymer Fiber Application," <i>IEEE Photonics Technology</i> 16 (4), 713-715 (1996)
	BX	Fundamentals of Semiconductor Physics and Devices, World Scientific Publishing Co., Pte. Ltd. (1997), pp. 38-41
	BY	Stringfellow, G.B. and Craford, eds., "High Brightness Light Emitting Diodes," Semiconductors and Semimetals, Academic Press (1997)
	BZ	Morgan, D.V., "Annealing effects on opto-electronic properties of sputtered and thermally evaporated indium-tin-oxide films," <i>Thin Solid Films</i> 312 , 268-272 (1998)
	CA	Qingke, Z., "Manufacture of AlGaInP Visible Light-Emitting Diodes By MOCVD & VPE," 42 (4), 993-995 (1994)
	CB	Chang, S.J. et al., "650 nm AlGaInP/GaInP Compressively Strained Multi-Quantum Well Light Emitting Diodes," <i>Jpn. J. Appl. Phys.</i> 37 , 653-655 (1998)
	CC	Chang, C.S. et al., "AlGaInP/GaInP multiquantum well light emitting diodes with an intentionally doped active layer," Dept. of Electrical Engineering, National Cheng Kung University
	CD	Civil Docket For Case No. 4:02-cv-05077-CW, pp. 1-69 (2004)

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